

28. (Added) The method of claim 24, further comprising forming a barrier layer overlying the support structures and within the openings prior to forming the conductive layer, wherein the barrier layer electrically contacts the uppermost copper bond pad.

29. (Added) The method of claim 28, wherein the barrier layer is further characterized as a tantalum barrier layer.

30. (Added) The method of claim 29, wherein the conductive film is further characterized as an aluminum film.

31. (Added) The method of claim 28, wherein the barrier layer includes a material selected from a group consisting of titanium, chromium, tantalum nitride, titanium nitride, and chromium nitride,

REMARKS

Claims 24-31 have been added. Applicants submit the amendment does not add new matter to the current Application. Applicants believe that the current application is in condition for allowance. Please feel free to contact me at the number below if there are any issues regarding this amendment or the current Application.

Respectfully submitted,

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Date

  
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